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(54) HEATING BODY OF EPITAXIAL GROWTH DEVICE

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(57)ABSTRACT

A heating body of an epitaxial growth device is provided. The heating body (1) includes a supporting base (11) and a tray (2). The supporting base (11) extends along an axis of the epitaxial growth device (100). The tray (2) is mounted on the supporting base (11) to support a substrate. The supporting base (11) is configured to generate heat by an electromagnetic induction with an induction coil, which in turn heats the tray (2). The tray (2) is configured to transfer heat to the substrate to heat the substrate. The supporting base (11) is provided with a temperature control channel (3), which is close to an edge of the tray (2), and along a direction perpendicular to a surface of the supporting base (11), a part of a projection of the temperature control channel (3) is on the tray (2).

